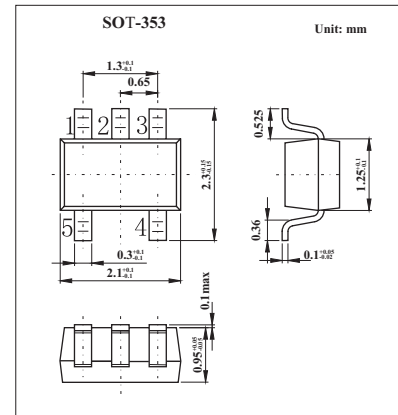
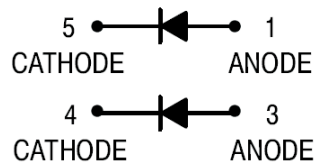


## High Voltage Switching Diode BAS21DW5T1

### ■ Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- High Conductance
- For General Purpose Switching Applications



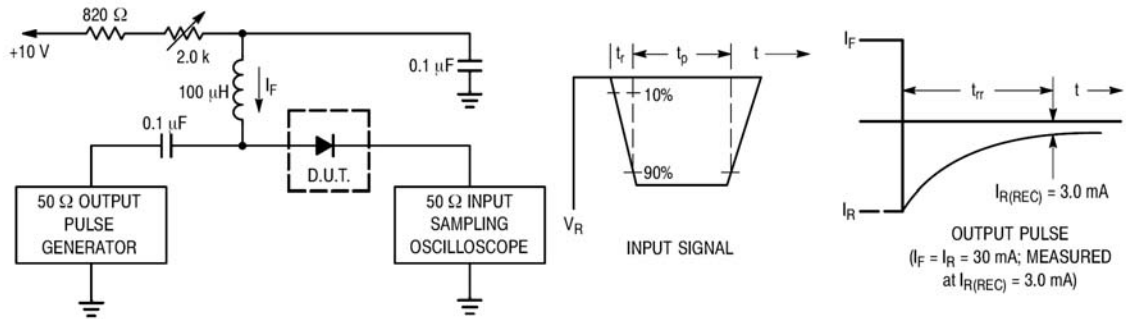
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	$V_R$	250	V
Peak Reverse Voltage	$V_{RRM}$	250	V
Forward Current	$I_F$	200	mA
Power Dissipation	$P_D$	385	mW
Operating Junction Temperature Range	$T_J$	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R = 100 \mu\text{A}$	250			V
Forward Voltage	$V_F$	$I_F = 100\text{mA}$			1.0	V
		$I_F = 200\text{mA}$			1.25	
Reverse Leakage	$I_R$	$V_R = 200\text{V}$			0.1	$\mu\text{A}$
		$V_R = 200\text{V}, T_J = 150^\circ\text{C}$			100	$\mu\text{A}$
Junction Capacitance	$C_j$	$V_R = 0\text{V}, f = 1.0\text{MHz}$			5.0	pF
Reverse Recover Time	$T_{rr}$	$I_F = I_R = 30 \text{mA}, I_{R(REC)} = 3.0 \text{mAdc}, R_L = 100 \Omega$			50	nS

### BAS21DW5T1



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 30 mA.
- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 30 mA.
- 3.  $t_p \gg t_{rr}$

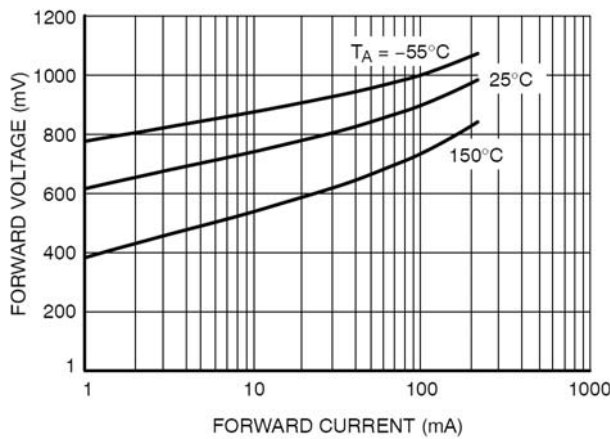


Figure 2. Forward Voltage

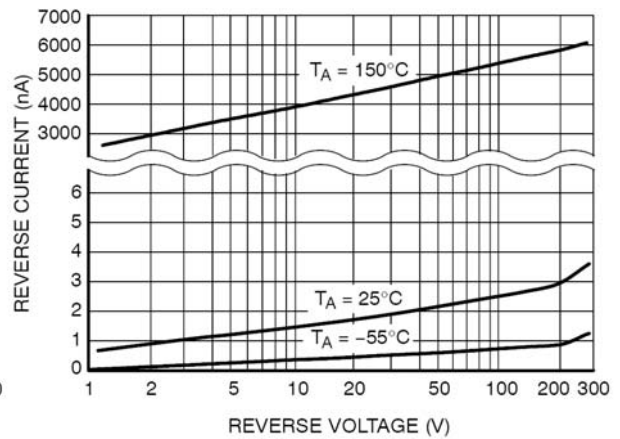


Figure 3. Reverse Leakage